

L Number	Hits	Search Text	DB	Time stamp
5	1	("5904538").PN.	USPAT; US-PGPUB	2003/03/08 15:17
6	4	("4523369"   "4534824"   "4570325"   "5229316").PN.	USPAT	2003/03/08 14:29
7	11	5904538.URPN.	USPAT	2003/03/08 14:30
8	1914	((438/243) or (438/244) or (438/424) or (438/430) or (438/435) or (438/524)).CCLS.	USPAT; US-PGPUB	2003/03/08 15:18
9	107062	fluorine	USPAT; US-PGPUB	2003/03/08 15:19
10	4562	ion adj implant	USPAT; US-PGPUB	2003/03/08 15:20
11	127	((438/243) or (438/244) or (438/424) or (438/430) or (438/435) or (438/524)).CCLS.) and fluorine	USPAT; US-PGPUB	2003/03/08 15:20
12	81593	tilt	USPAT; US-PGPUB	2003/03/08 15:21
13	4	((438/243) or (438/244) or (438/424) or (438/430) or (438/435) or (438/524)).CCLS.) and fluorine) and tilt	USPAT; US-PGPUB	2003/03/08 15:21
-	743	(438/424).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 11:03
-	4	((438/424).CCLS.) and PMOSFET	USPAT; US-PGPUB	2002/05/01 11:16
-	3	((438/424).CCLS.) and PMOSFET) and (sti or (shallow adj trench adj isolation))	USPAT; US-PGPUB	2002/05/01 11:05
-	2	((438/424).CCLS.) and PMOSFET) and (sti or (shallow adj trench adj isolation))	USPAT; US-PGPUB	2002/05/01 11:07
-	2	and ((gate with gate adj oxide) and liner) ((((438/424).CCLS.) and PMOSFET) and (sti or (shallow adj trench adj isolation))	USPAT; US-PGPUB	2002/05/01 11:08
-	0	and ((gate with gate adj oxide) and liner)) and (hdp or(high adj density adj plasma))	USPAT; US-PGPUB	2002/05/01 11:08
-	2	((438/424).CCLS.) and PMOSFET) and (sti or (shallow adj trench adj isolation))) and ((gate with gate adj oxide) and liner)) and (hdp or(high adj density adj plasma))) and (tilt\$3 adj angle\$1)	USPAT; US-PGPUB	2002/05/01 11:11
-	1	((438/424).CCLS.) and PMOSFET) and (sti or (shallow adj trench adj isolation))) and ((gate with gate adj oxide) and liner)) and (hdp or(high adj density adj plasma))) and implant\$3) and angle\$1	USPAT; US-PGPUB	2002/05/01 11:12
-	4	((438/424).CCLS.) and PMOSFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 12:17
-	21280	PMOS or PMOSFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 12:18
-	2647	( PMOS or PMOSFET) and (sti or (shallow trench))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 12:27

-	1687	(( PMOS or PMOSFET) and (sti or (shallow trench))) and (gate with (gate adj oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 12:27
-	0	((( PMOS or PMOSFET) and (sti or (shallow trench))) and (gate with (gate adj oxide))) and ((liner adj layer) and oxidat\$3)) and (hdp or (high adj density adj plasma))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 12:23
-	174	( PMOS or PMOSFET) and (hdp or (high adj density adj plasma))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 12:23
-	174	( PMOS or PMOSFET) and (( PMOS or PMOSFET) and (hdp or (high adj density adj plasma)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 12:24
-	0	((( PMOS or PMOSFET) and (sti or (shallow trench))) and (gate with (gate adj oxide))) and ((liner adj layer) and oxidat\$3)) and (( PMOS or PMOSFET) and (hdp or (high adj density adj plasma)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 12:25
-	7	(( PMOS or PMOSFET) and (sti or (shallow trench))) and (gate with (gate adj oxide))) and ((liner adj layer) and oxidat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 12:26
-	104	(( PMOS or PMOSFET) and (( PMOS or PMOSFET) and (hdp or (high adj density adj plasma)))) and trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 12:26
-	0	(( PMOS or PMOSFET) and (( PMOS or PMOSFET) and (hdp or (high adj density adj plasma)))) and trench) and ((liner adj layer) and oxidat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 12:26
-	54	(( PMOS or PMOSFET) and (( PMOS or PMOSFET) and (hdp or (high adj density adj plasma)))) and trench) and (gate with (gate adj oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 12:27
-	54	((( PMOS or PMOSFET) and (( PMOS or PMOSFET) and (hdp or (high adj density adj plasma)))) and trench) and (gate with (gate adj oxide))) and (sti or (shallow trench))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 12:28
-	29	(((( PMOS or PMOSFET) and (( PMOS or PMOSFET) and (hdp or (high adj density adj plasma)))) and trench) and (gate with (gate adj oxide))) and (sti or (shallow trench))) and angle\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 12:29
-	2	(((( PMOS or PMOSFET) and (( PMOS or PMOSFET) and (hdp or (high adj density adj plasma)))) and trench) and (gate with (gate adj oxide))) and (sti or (shallow trench))) and angle\$1) and tilt\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 12:29
-	2	(((( PMOS or PMOSFET) and (( PMOS or PMOSFET) and (hdp or (high adj density adj plasma)))) and trench) and (gate with (gate adj oxide))) and (sti or (shallow trench))) and angle\$1) and tilt\$3) and implant\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 15:39

-	0	((((( PMOS or PMOSFET) and (( PMOS or PMOSFET) and (hdp or (high adj density adj plasma)))) and trench) and (gate with (gate adj oxide))) and (sti or (shallow trench))) and angle\$1) and tilt\$3) and implant\$3 and (F or (fluoride\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 16:19
-	0	((((( PMOS or PMOSFET) and (( PMOS or PMOSFET) and (hdp or (high adj density adj plasma)))) and trench) and (gate with (gate adj oxide))) and (sti or (shallow trench))) and angle\$1) and tilt\$3) and implant\$3 and (F or (fluoride\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 15:44
-	614	(ion adj implant\$3) with (F or (fluoride\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 16:21
-	0	((ion adj implant\$3) with (F or (fluoride\$1))) and (((((( PMOS or PMOSFET) and (( PMOS or PMOSFET) and (hdp or (high adj density adj plasma)))) and trench) and (gate with (gate adj oxide))) and (sti or (shallow trench))) and angle\$1) and tilt\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 15:47
-	1	((ion adj implant\$3) with (F or (fluoride\$1))) and (PMOS or PMOSFET) ) and (hdp or (high adj density adj plasma))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 15:49
-	6	(((((ion adj implant\$3) with (F or (fluoride\$1))) and (PMOS or PMOSFET) ) and (gate with (gate adj oxide)) ) and angle\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 15:54
-	2	(((((ion adj implant\$3) with (F or (fluoride\$1))) and (PMOS or PMOSFET) ) and (gate with (gate adj oxide)) ) and angle\$1) and tilt\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 15:55
-	48	(((((ion adj implant\$3) with (F or (fluoride\$1))) and (PMOS or PMOSFET) ) and (gate with (gate adj oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 16:02
-	9	(((((ion adj implant\$3) with (F or (fluoride\$1))) and (PMOS or PMOSFET) ) and (gate with (gate adj oxide)) ) and trench\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 16:03
-	62	((ion adj implant\$3) with (F or (fluoride\$1))) and (PMOS or PMOSFET)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 16:11
-	18	((ion adj implant\$3) with (F or (fluoride\$1))) with trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 16:14
-	21280	PMOS or PMOSFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 16:54
-	242	(PMOS or PMOSFET) and tilt\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 16:20

-	1	((PMOS or PMOSFET) and tilt\$3) and ((ion adj implant\$3) with (fluoride\$1))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 16:58
-	0	(PMOS or PMOSFET) and (implant\$3 adj sidewalls)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 16:56
-	0	(PMOS or PMOSFET) and (implant\$3 same sidewalls)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 16:56
-	0	(PMOS or PMOSFET) and (implant\$3 with sidewalls)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 16:56
-	3	(PMOS or PMOSFET) and (implant\$3 and sidewalls)	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 16:57
-	7	(PMOS or PMOSFET) and sidewall\$1	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 16:58
-	1589	(PMOS or PMOSFET) and trench	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 16:58
-	7	((PMOS or PMOSFET) and trench) and ((ion adj implant\$3) with (fluoride\$1))	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 17:00
-	1	((PMOS or PMOSFET) and trench) and (implant\$3 with (fluoride\$1)) with angle\$1	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 17:12
-	12	((PMOS or PMOSFET) and trench) and (implant\$3 with (angle\$1 or (tilt\$3))) and fluoride\$1	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 17:12
-	162	((PMOS or PMOSFET) and trench) and (implant\$3 with (angle\$1 or (tilt\$3)))	USPÄT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/05/01 17:21
-	115	((09/801,233) or (09/745,125) or (09/639,579 ) or (09/639,702 ) or (09/639,749 ) or (60/279,855)).CCLS.	USPAT; US-PGPUB	2002/05/01 18:09
-	0	(("9801233") or ("9745125") or ("9639579") or ("9639702") or ("9639749") or ("60279855")).PN.	USPAT; US-PGPUB	2002/05/01 18:11
-	9	(("5768192") or ("5535156") or ("6015738") or ("5909622") or ("5943576") or ("6080629") or ("6117715") or ("6140191") or ("6187643")).PN.	USPAT; US-PGPUB	2002/05/01 18:16
-	1	"5786256".PN.	USPAT; US-PGPUB	2002/05/01 18:18
-	1	"5766998".PN.	USPAT; US-PGPUB	2002/05/01 18:18
-	1	"5670392".PN.	USPAT; US-PGPUB	2002/05/01 18:19